TECHNICAL DATA

LONGLITE® DRY FILM PHOTO RESIST

FF-9075S

SUMMARY

LONGLITE® Dry Film Photo Resist FF-9075S is negative working and aqueous photo polymer. FF-9075S is suitable for the applications of acidic etching, tenting, copper / tin plating, and copper / tin-lead plating in PCB manufacturing.

FEATURES

- 1. Excellent adhesion and conformation capability.
- 2. Excellent chemical resistance for plating application.
- 3. Excellent resolution characteristics.
- 4. Wilder latitude for exposure.
- 5. Wider margin in development.
- 6. High tenting reliability.
- 7. Low sludge in development bath.
- 8. Less contamination to plating bath.

SPECIFICATION

FF-9075S $75 \mu m \equiv 2 \mu m$

Standard width interval: 0.125 inch.

Standard length: 500 ft / roll

STORAGE AND SAFTY HANDLING

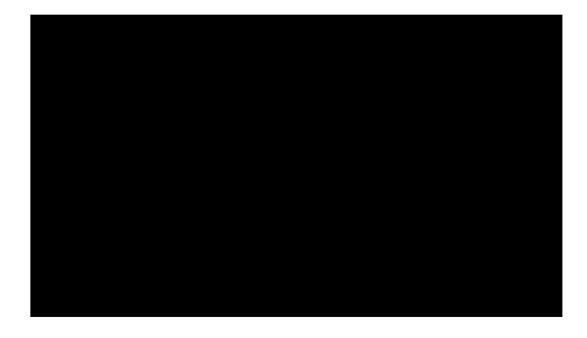
- Store horizontally in a cool and dry warehouse with temperature 5~20°C and RH 50±10%.
- Safe to use under UV-cut yellow fluorescent lamps. When not using, seal by black sheet such as its original black plastic packing sheet, and lay down dry film rolls horizontally for storage.
- Lamination will cause vapor, use in room with adequate ventilation.
- Avoid contacting the resist layer of dry film with skin directly which may cause irritation. Wash with soap and water thoroughly after handling. If persistent irritation occurs, consult a physician.

SENSITIVITY AT VARIOUS EXPOSURE ENERGIES

Grade		FF-9075S	
Developing time		96 sec (B.P 48sec)	
Exposure Energy mJ/cm ²	20	6	
	30	7	
	40	8	
	50	9	
	60	9. 5	
	70	10	
	80	10.5	
	90	11	
	100	11.5	

*Data for reference

* Exposure was given by placing Stouffer 21 step guide directly in contact with DFR, and counted the steps still remaining after development.

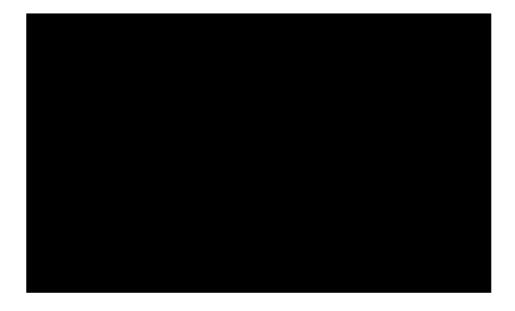


RESOLUTION AT VARIOUS EXPOSURE ENERGIES

Grade		FF-9075S Space (μm)		
30	60			
40	60			
50	80			
60	80			
70	100			
80	125			
90	150			
100	150			

*Data for reference

 \divideontimes Test pattern: CCP Pattern 1 (L/S = 1/2), from 20 to 200 μ m 5 "L" shape lines each.

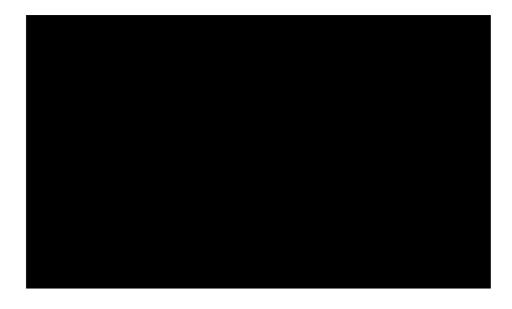


ADHESION AT VARIOUS EXPOSURE ENERGIES

Grade		FF-9075S Line (µm)		
Exposure Energy mJ/cm ²	20	125		
	30	100		
	40	80		
	50	60		
	60	60		
	70	60		
	80	50		
	90	50		
	100	50		

*Data for reference

 $\mbox{\ensuremath{\mbox{\%}}}$ Test pattern: CCP Pattern 1 (L/S = 2/1), from 20 to 200 μm 5 "L" 1shape lines each.



<u>VARIATION IN RESIST WIDTH AT VARIOUS EXPOSURE ENERGIES</u>

Grade		FF-9075S	
		Width Variation (μm)	
Exposure Energy mJ/cm²	20	-5	
	30	-2	
	40	0	
	50	2	
	60	5	
	70	5	
	80	10	
	90	15	
	100	18	

*Data for reference

% Measuring resist width variation from test pattern after development. Test pattern L/S= 100 / $200 \mu m$.



STRIPPING

		Stripping time (sec)		Stripped piece			
Stripper	NaOH	2%	3%	4%	2%	3%	4%
Temperature	50°C	157"	150"	144"	MS	MS	L
remperature	55°C	151"	141"	127"	MS	M	ML
	60°C	141"	128"	120"	M	ML	ML

*Data for reference

※ Exposure : 40 mj/cm². (Step 8by SST 21 step)

Tested by dipping. Stripped piece size:

LL :sheet

L: about 3 cm
ML: about 2 cm.
M: about 1 cm.
MS: about 0.5 cm
S: about 0.3 cm

TENTING

strength (g)	590.1	
Time(sec)	4.37	

Remark:

a. Data for reference

b. Step: 8 Step

c. Gauge: $\phi 2mm$.

d. Speed: 10mm/min.

e. Board: φ6mm, thickness 1.6mm.

RECOMMENDED OPERATION CONDITIONS

• Surface protreatment:

Method Inner: Chemical brush, Pumice brush

Outer: Buffering brush + Pumice brush

Water break test: At least 15~30 sec (vertically)

▶ Don't dry board with hot air directly while the board surface still has water on it.

► Recommended surface roughness: $R_a=0.2\sim0.4 \mu m$, $R_z=1.5\sim2.5 \mu m$

Lamination:

Roll temperature: 110±10℃ $3\sim5 \text{ kg/cm}^2$ Pressure: 1.0~3.0 m/min Speed: Seal bar temperature: 55~65℃ Seal bar pressure: $2\sim5 \text{ kg/cm}^2$ Seal time: 1.5~2 sec 40~60℃ Board temperature before lamination: 45~55℃ Board temperature after lamination:

Holding time① 15 min~2days (23±2°C, 50±10% RH)

▶ The temperature and pressure of the roll should be adjusted in accordance with the structure of the particular laminator.

▶ To shade the panels when leaving them for more than six hours under a UV-free yellow light.

Exposure:

Energy: $30\sim60 \text{ mj/cm}^2$

Step: 7~9 step of Stouffer Sensitivity Tablet 21 step Holding time 15 min~2days. (23±2°C, 50±10% RH)

► Holding time① + Holding time② < 4 days

Development:

Developer: 0.8~1.2 wt% Na₂CO₃

Temperature: $26\sim30^{\circ}\text{C}$ Pressure: $1.2\sim2.0 \text{ kg/cm}^2$ Break point: $1/2\sim2/3$

▶ Water rinsing after development is recommended to be done at 15-25 °C and a spray pressure of 1.2-2.0 kg/cm²

► Keep the pH of rinsing water in the first tank below 8.5

► The loading content for resist should be adjusted to 6g/l or less.

• Etching:

Type Acidic

Etchant: Cupric chloride or Ferric chloride

• <u>Stripping</u>

Stripper: 2.5~3.0% NaOH or KOH

Temperature: $50\pm5^{\circ}$ C

Pressure: $1.0\sim3.0 \text{ kg/cm}^2$

Lifting point: $1/2\sim2/3$

▶ The loading content of resist should be adjusted to 20g/l or less.

▶ Water rinsing after stripping is recommended to be done at spray pressure of 1.0kg/cm² or more.